Ref #	Hits	Search Query	DBs	Default Operator	Plurais	Time Stamp
L1	89	("20020009274" "20020158263" "20 040061126" "20040195572" "33480 56" "3976877" "4058821" "4612083 " "4766471" "4811210" "4830444" " 4843587" "4851695" "488625" "48 94699" "4988891" "5008554" "5095 380" "5249245" "5262980" "526679 4" "5268679" "5291324" "5297232" "5339090" "5353247" "5357122" " 5362961" "5383042" "5410502" "54 78658" "5491571" "5523704" "5546 209" "5583570" "5654559" "573873 1" "5832147" "5848214" "6111902" "6160828" "6627953" "6661940"). PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 11:03
L2	2	"US 20040061126"	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2006/08/15 09:13
L3	17	(("4888625") or ("3348056") or ("3976877") or ("4058821") or ("4851695") or ("4612083") or ("5249245")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/15 11:59
L4	91	349/17.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 12:04
L5	241	257/113.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OŅ	2006/08/15 12:05
L6	3	L5 and liquid adj crystal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 12:07
L7	2	L6 and (TFT thin adj film adj transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 12:06

L8	1	L7 and (IC integrated adj circuit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 12:05
L9	1	L8 and(amorphous silicon photodiode phototransistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 12:06
L10	483059	(liquid adj crystal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 12:07
L11	57770	L10 and (TFT thin adj film adj transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 12:07
L12	12526	L11 and (integrated adj circuit IC)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 12:44
L13	10	L12 and (amorphous near2 silicon near2 photodiode phototransitor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 12:37
L14	8340	L12 and (amorphous silicon photodiode phototransitor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 12:08
L15	124	L12 and (amorphous silicon) same (photodiode phototransitor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 12:52

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L16	37	L15 and cathode same anode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 12:09		
L17	4478	385/14.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 12:38		
L18	175	385/14.ccls. and liquid adj crystal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/15 12:38		
L19	26	(("5262980") or ("5353247") or ("5410502") or ("5339090") or ("5095380") or ("4830444") or ("5291324") or ("5523704") or ("4811210") or ("4843587") or ("6661940") or ("5832147") or ("5008554")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/15 12:59		
L20	2	("5268679").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/15 12:59		
L22	21	(US-20060141645-\$ or US-20050168491-\$ or US-20050045881-\$ or US-20050041002-\$ or US-20050030264-\$ or US-20040252867-\$ or US-20040113548-\$ or US-20040043676-\$ or US-20040042707-\$ or US-20040042707-\$ or US-20020057055-\$ or US-20040056180-\$).did. or (US-5410502-\$ or US-5268679-\$ or US-4830444-\$ or US-4766471-\$ or US-4612083-\$ or US-6933529-\$ or US-6300612-\$).did. or (JP-2004247405-\$).did.	US-PGPUB; USPAT; DERWENT	OR	ON	2006/08/15 15:00		
L23	13	L22 and cathode and anode and amorphous and (tft thin adj film adj transistor)	US-PGPUB; USPAT; DERWENT	OR	ON	2006/08/15 15:06		

L24	5	L22 and cathode and anode and amorphous and (tft thin adj film adj transistor) and (semiconductor) and (gate adj electrode) and (gate adj insulat\$5)	US-PGPUB; USPAT; DERWENT	OR	ON	2006/08/15 15:27
L25	1	cathode same anode same amorphous same (tft thin adj film adj transistor) same (semiconductor) same (gate adj electrode) same (gate adj insulat\$5)	US-PGPUB; USPAT; DERWENT	OR	ON	2006/08/15 15:42
L26	145	cathode same anode same amorphous same (tft thin adj film adj transistor)	US-PGPUB; USPAT; DERWENT	OR	ON	2006/08/15 15:43
L27	9	"US 6664732"	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2006/08/15 16:00

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